

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	51	ding near yi.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 15:05	
2	BRS	L2	2	6355524.pn.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 15:13	
3	BRS	L3	2	5668757.pn.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 15:13	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	11	(peripheral near5 gate) near25 (select near gate) near35 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 15:26	
5	BRS	L5	203	(select near gate) near35 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:17	
6	BRS	L6	40	select near gate near dielectric	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:23	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L8	74	(select near gate) near30 (transistor) near25 (thickness)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 16:24	
8	BRS	L7	1820	(select near gate) near30 (transistor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 16:48	
9	BRS	L9	536	(select near gate) near30 (gate) near (dielectric or insulat\$ or oxide\$1)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/07 16:49	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	384	(select near gate) near30 (gate) near (dielectric or insulat\$ or oxide\$1) and (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:50	
11	BRS	L11	17517 96	(select near gate) near30 (gate) near (dielectric or insulat\$ or oxide\$1) nea25 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:50	
12	BRS	L12	17517 84	(select near gate) near30 ((gate) near (dielectric or insulat\$ or oxide\$1)) nea25 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:51	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	17517 84	(select near gate) near30 ((gate) near (dielectric or insulat\$ or oxide\$1)) nea25 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:51	
14	BRS	L14	17517 84	((select near gate)) near30 ((gate) near (dielectric or insulat\$ or oxide\$1)) nea25 (thickness)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:51	
15	BRS	L15	17517 84	((select near gate)) near30 ((gate) near (dielectric or insulat\$ or oxide\$1)) nea25 ((thickness))	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:51	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	491	((select near gate)) near30 ((gate) near (dielectric or insulat\$ or oxide\$1))	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/07/0 7 16:52	

	U	1	Document ID	Title	Current OR	Pages
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6344993 B1	Dual floating gate EEPROM cell array with steering gates shared by adjacent cells	365/185.01	16
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6266278 B1	Dual floating gate EEPROM cell array with steering gates shared adjacent cells	365/185.18	16
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6151248 A	Dual floating gate EEPROM cell array with steering gates shared by adjacent cells	365/185.14	18